

Supporting Information

Ba₆Zn₇Ga₂S₁₆: A Wide Band Gap Sulfide with Phase-Matchable Infrared NLO Properties

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Table S1. Properties comparison of the known phase-matchable (PM) IR NLO chalcogenides with $E_g > 3.0$ eV, AgGaS_2 and title $\text{Ba}_6\text{Zn}_7\text{Ga}_2\text{S}_{16}$.

	Materials	E_g (eV)	LDT ($\times \text{AGS}$)	d_{ij} ($\times \text{KDP}$)
①	$\text{Ba}_6\text{Zn}_7\text{Ga}_2\text{S}_{16}$ ^(this work)	3.5	28^a	17
②	SnGa_4S_7 ^{S1}	3.1	19^a	43.3
③	BaGa_4S_7 ^{S2}	3.54	3^b	33.3
④	$\text{Na}_2\text{BaSnS}_4$ ^{S3}	3.27	5^a	10
⑤	$\text{Na}_2\text{BaGeS}_4$ ^{S4}	3.7	8^a	17
⑥	$\text{Na}_2\text{ZnGe}_2\text{S}_6$ ^{S4}	3.25	6^a	30
⑦	LiInS_2 ^{S5, S6}	3.57	2.5^b	19
⑧	LiGaS_2 ^{S5, S7}	4.15	11^b	15
⑨	AgGaS_2 ^{S8}	2.64	1^a	33.3
	$\text{BaGa}_2\text{SiS}_6$ ^{S9}	3.75	-	33.3
^a Measured on polycrystalline samples, ^b Measured on large single crystals.				

References:

- (S1) Luo, Z. Z.; Lin, C. S.; Cui, H. H.; Zhang, W. L.; Zhang, H.; He, Z. Z.; Cheng, W. D. SHG materials SnGa_4Q_7 (Q = S, Se) appearing with large conversion efficiencies, high damage thresholds, and wide transparencies in the mid-infrared region. *Chem. Mater.* **2014**, *26*, 2743–2749.
- (S2) Lin, X. S.; Zhang, G.; Ye, N. Growth and characterization of BaGa_4S_7 : a new crystal for mid-IR nonlinear optics. *Cryst. Growth Des.* **2009**, *9*, 1186–1189.
- (S3) Li, G. M.; Wu, K.; Liu, Q. Yang, Z. H.; Pan, S. L. $\text{Na}_2\text{ZnGe}_2\text{S}_6$: a new infrared nonlinear optical material with good balance between large second-harmonic generation response and high laser damage threshold. *J. Am. Chem. Soc.* **2016**, *138*, 7422–7428.
- (S4) Wu, K.; Yang, Z. H.; Pan, S. L. Na_2BaMQ_4 (M = Ge, Sn; Q = S, Se): Infrared Nonlinear Optical Materials with Excellent Performances and that Undergo Structural Transformations. *Angew. Chem. Int. Ed.* **2016**, *128*, 6825–6827.
- (S5) Isaenko, L. I.; Vasilyeva, I. G.; Merkulov, A. A.; Yelisseyev, A. P.; Lobanov, S. I. Growth of new nonlinear crystals LiMX_2 (M = Al, In, Ga; X = S, Se, Te) for the mid-IR optics. *J. Cryst. Growth.* **2005**, *275*, 217–223.
- (S6) Fossier, S.; Salaun, S.; Mangin, J.; Bidault, O.; Thenot, I.; Zondy, J. J.; Chen, W. D.; Rotermund, F.; Petrov, V.; Petrov, P.; Henningsen, J.; Yelisseyev, A.; Isaenko, L.; Lobanov, S.; Balachninaite, O.; Sleky, G.; Sirutkaitis, V. Optical, vibrational, thermal, electrical, damage, and phase-matching properties of lithium thioindate. *J. Opt. Soc. Am. B.* **2004**, *21*, 1981–2007.
- (S7) Tyazhev, A.; Vedenyapin, V.; Marchev, G.; Isaenko, L.; Kolker, D.; Lobanov, S.; Petrov, V.; Yelisseyev, A.; Starikova, M.; Zondy, J. Singly-resonant optical parametric oscillation based on the wide band-gap mid-IR nonlinear optical crystal LiGaS_2 . *J. Opt. Mater.* **2013**, *35*, 1612–1615.
- (S8) Harasaki, A.; Kato, K. J. New data on the nonlinear optical constant, phase-matching, and optical damage of AgGaS_2 . *Appl. Phys.* **1997**, *36*, 700–703.
- (S9) Yin, W. L.; Feng, K.; He, R.; Mei, D. J.; Lin, Z. S.; Yao, J. Y.; Wu, Y. C. BaGa_2MQ_6 (M = Si, Ge; Q = S, Se): a new series of promising IR nonlinear optical materials. *Dalton Transactions*,

2012, *41*, 5653–5661.

Table S2. Atomic coordinates and equivalent isotropic displacement parameters of Ba₆Zn₇Ga₂S₁₆.

Atom	Wyckoff site	<i>x</i>	<i>y</i>	<i>z</i>	$U_{eq}(\text{\AA})^a$
Ba(1)	9 <i>b</i>	0.35464(6)	0.08476(6)	0.24496(2)	0.0164(2)
Ba(2)	9 <i>b</i>	0.43443(7)	0.40462(7)	0.11452(2)	0.0179(2)
Zn(1)	9 <i>b</i>	0.3079(2)	0.4365(2)	0.31272(4)	0.0118(2)
Zn(2)	9 <i>b</i>	0.0303(2)	0.2189(2)	0.04426(4)	0.0116(2)
Zn(3)	3 <i>a</i>	0.0000	0.0000	0.3589(3)	0.019(2)
Zn(3')	3 <i>a</i>	0.0000	0.0000	0.3350(9)	0.014(4)
Ga(1)	3 <i>a</i>	0.0000	0.0000	0.53637(7)	0.0114(4)
Ga(2)	3 <i>a</i>	0.0000	0.0000	0.15744(7)	0.0108(4)
S(1)	9 <i>b</i>	0.4432(2)	0.1379(2)	0.01614(8)	0.0142(4)
S(2)	9 <i>b</i>	0.3337(3)	0.4409(3)	0.2278(2)	0.0151(5)
S(3)	9 <i>b</i>	0.2555(2)	0.1958(2)	0.34590(7)	0.0099(4)
S(4)	9 <i>b</i>	0.2270(3)	0.0136(3)	0.1288(2)	0.0169(6)
S(5)	3 <i>a</i>	0.0000	0.0000	0.0000(2)	0.0123(6)
S(6)	3 <i>a</i>	0.0000	0.0000	0.4530(2)	0.0132(8)
S(7)	3 <i>a</i>	0.0000	0.0000	0.2394(2)	0.0134(9)
S(8)	3 <i>a</i>	0.0000	0.0000	0.8464(2)	0.0126(5)

^a U_{eq} is defined as one-third of the trace of the orthogonalized U_{ij} tensor.

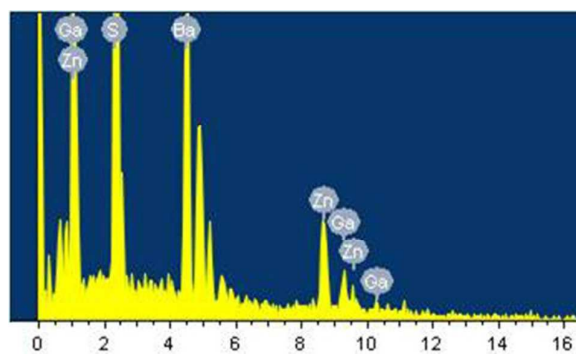


Figure S1. The EDX spectrum of $\text{Ba}_6\text{Zn}_7\text{Ga}_2\text{S}_{16}$.

Table S3. The ICP data of $\text{Ba}_6\text{Zn}_7\text{Ga}_2\text{S}_{16}$.

Comp.	Element	Weight%	Formula
$\text{Ba}_6\text{Zn}_7\text{Ga}_2\text{S}_{16}$	Ba	47.85%	$\text{Ba}_{5.9}\text{Zn}_{7.2}\text{Ga}_{2.0}$
	Zn	28.02%	
	Ga	8.25%	

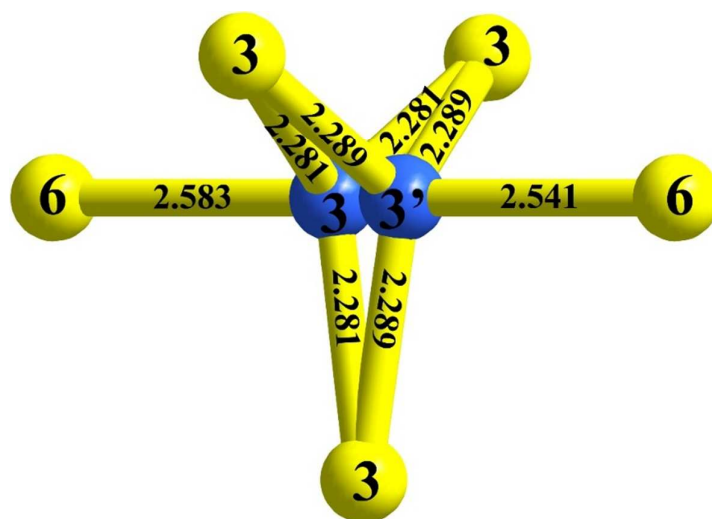


Figure S2. The coordination environments of Zn on Wyckoff site 3e that splitting into Zn(3) (occu.: 0.80) and Zn(3') (occu.: 0.20) with Zn–S bond length (Å) marked.

PS: The possible existing Zn(3') (occu.: 0.20) atom is very close to Zn(3), with the Zn(3)–Zn(3') distance being 0.65 Å. Additionally, the Zn(3')–S bond distances and the S–Zn(3')–S angles of the Zn(3')S₄ tetrahedron are similar to the corresponding data of the Zn(3)S₄ tetrahedron. Similar positional disorder has been found on the In atom which splits into In(2) (occu.: 0.80) and In(3) (occu.: 0.20) of compound Ba₁₂In₄S₁₉^{S10} and the Cu atom with Cu(1) (occu.: 0.82) and Cu(2) (occu.: 0.18) of compound R₂CuInS₅ (R = La, Ce, Pr, Nd and Sm).^{S11}

References:

- (S10) Liu, J. W.; Wang, P.; Chen, L. Contribution of disulfide S₂²⁻ anions to the crystal and electronic structures in ternary sulfides, Ba₁₂In₄S₁₉, Ba₄M₂S₈ (M= Ga, In). *Inorg. Chem.* **2011**, *50*, 5706–5713.
- (S11) Jin, G. B.; Choi, E. S.; Guertin, R. P.; Booth, C. H.; Albrecht-Schmitt, T. E. Syntheses, structure, magnetism, and optical properties of the ordered interlanthanide copper chalcogenides Ln₂YbCuQ₅ (Ln= La, Ce, Pr, Nd, Sm; Q= S, Se): evidence for unusual magnetic ordering in Sm₂YbCuS₅. *Chem. Mater.* **2011**, *23*, 1306–1314.

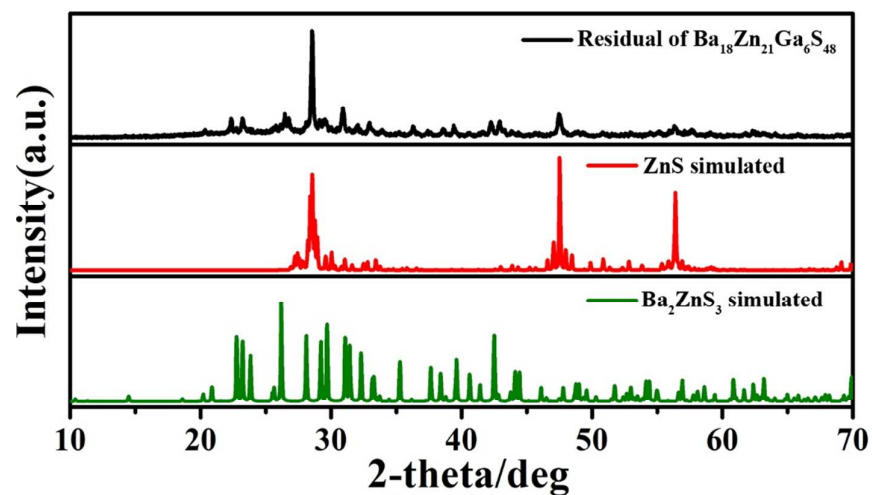


Figure S3. Powder X-ray diffraction patterns of samples obtained after TG and DTA measurements of $\text{Ba}_6\text{Zn}_7\text{Ga}_2\text{S}_{16}$, indicating that this compound was mainly decomposed into ZnS and Ba_2ZnS_3 .

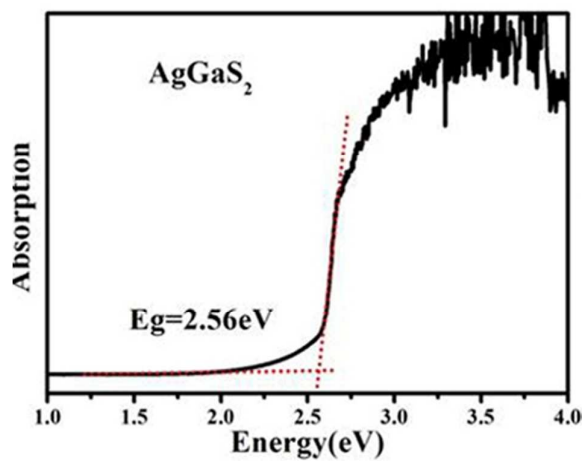


Figure S4. Diffuse reflection spectra of AgGaS_2 .

Table S4. Selected bond lengths (Å) of Ba₆Zn₇Ga₂S₁₆.

Bond	dist.	bond	dist.
Ba(1)–S(1)	3.422(2)	Zn(2)–S(1)	2.319(2)
Ba(1)–S(2)	3.387(2)	Zn(2)–S(3)	2.335(2)
Ba(1)–S(2)	3.591(2)	Zn(2)–S(4)	2.319(3)
Ba(1)–S(2)	3.617(3)	Zn(2)–S(5)	2.337(2)
Ba(1)–S(3)	3.255(2)	Zn(3)–Zn(3')	0.65(2)
Ba(1)–S(4)	3.319(3)	Zn(3)–S(3)	2.290(2)
Ba(1)–S(5)	3.672(2)	Zn(3)–S(3)	2.290(2)
Ba(1)–S(7)	3.1383(6)	Zn(3)–S(3)	2.290(2)
Ba(1)–S(8)	3.301(3)	Zn(3)–S(6)	2.54(2)
Ba(2)–S(1)	3.458(2)	Zn(3')–S(3)	2.281(4)
Ba(2)–S(2)	3.285(3)	Zn(3')–S(3)	2.281(4)
Ba(2)–S(3)	3.187(2)	Zn(3')–S(3)	2.281(4)
Ba(2)–S(4)	3.333(3)	Zn(3')–S(7)	2.58(3)
Ba(2)–S(4)	3.544(3)	Ga(1)–S(2)	2.307(3)
Ba(2)–S(6)	3.1753(6)	Ga(1)–S(2)	2.307(3)
Ba(2)–S(8)	3.212(3)	Ga(1)–S(2)	2.307(3)
Zn(1)–S(1)	2.298(2)	Ga(1)–S(6)	2.252(5)
Zn(1)–S(1)	2.346(2)	Ga(2)–S(4)	2.289(3)
Zn(1)–S(2)	2.307(3)	Ga(2)–S(4)	2.289(3)
Zn(1)–S(3)	2.323(2)	Ga(2)–S(4)	2.289(3)
		Ga(2)–S(7)	2.213(5)

Table S5. Selected angles (deg) of Ba₆Zn₇Ga₂S₁₆.

bond	angle	bond	angle
S(1)–Zn(1)–S(2)	111.53(9)	S(3)–Zn(3')–S(3)	118.4(3)
S(1)–Zn(1)–S(3)	109.90(7)	S(3)–Zn(3')–S(3)	118.4(3)
S(2)–Zn(1)–S(3)	111.66(9)	S(3)–Zn(3')–S(3)	118.4(3)
S(1)–Zn(1)–S(1)	100.5(2)	S(3)–Zn(3')–S(7)	97.4(6)
S(2)–Zn(1)–S(1)	120.59(9)	S(3)–Zn(3')–S(7)	97.4(6)
S(3)–Zn(1)–S(1)	101.73(7)	S(3)–Zn(3')–S(7)	97.4(6)
S(1)–Zn(2)–S(4)	100.05(9)	S(6)–Ga(1)–S(2)	106.81(8)
S(1)–Zn(2)–S(3)	102.09(8)	S(6)–Ga(1)–S(2)	106.81(8)
S(4)–Zn(2)–S(3)	118.81(9)	S(2)–Ga(1)–S(2)	111.99(7)
S(1)–Zn(2)–S(5)	112.16(8)	S(6)–Ga(1)–S(2)	106.81(8)
S(4)–Zn(2)–S(5)	123.0(2)	S(2)–Ga(1)–S(2)	111.99(7)
S(3)–Zn(2)–S(5)	99.24(7)	S(2)–Ga(1)–S(2)	111.99(7)
S(3)–Zn(3)–S(3)	117.7(2)	S(7)–Ga(2)–S(4)	109.74(7)
S(3)–Zn(3)–S(3)	117.7(2)	S(7)–Ga(2)–S(4)	109.74(7)
S(3)–Zn(3)–S(3)	117.7(2)	S(4)–Ga(2)–S(4)	109.20(8)
S(3)–Zn(3)–S(6)	98.8(2)	S(7)–Ga(2)–S(4)	109.74(7)
S(3)–Zn(3)–S(6)	98.8(2)	S(4)–Ga(2)–S(4)	109.20(8)
S(3)–Zn(3)–S(6)	98.8(2)	S(4)–Ga(2)–S(4)	109.20(8)

Table S6. The direction and magnitude (Debye: D) of dipole moments of the building units in Ba₆Zn₇Ga₂S₁₆.

Building unit	X	Y	Z	Symmetry operation
Zn(3)S₄	0	0	0.65	
1 st Zn(1)S ₄	0.62	0.31	1.26	(X,Y,Z)
2 nd Zn(1)S ₄	-0.31	0.31	1.26	(-Y,X-Y,Z)
3 rd Zn(1)S ₄	-0.31	-0.62	1.26	(-X+Y,-X,Z)
Ga(1)S ₄	0	0	-1.98	
Zn(1)₃Ga(1)S₁₀	0	0	1.80	
1 st Zn(2)S ₄	-1.43	-1.61	-1.13	(X,Y,Z)
2 nd Zn(2)S ₄	1.61	0.18	-1.13	(-Y,X-Y,Z)
3 rd Zn(2)S ₄	-0.18	1.43	-1.13	(-X+Y,-X,Z)
Ga(2)S ₄	0	0	1.37	
Zn(2)₃Ga(2)S₁₀	0	0	-2.02	
A basic repeating unit of [Zn(1)₃Zn(2)₃Zn(3)Ga(1)Ga(2)S₂₂]	0	0	0.43	

Table S7. The results of polycrystalline LDTs for Ba₆Zn₇Ga₂S₁₆ and AgGaS₂ in the same particle size range of 150–210 μm.

Comp.	Damage energy (mJ)	Spot area (cm ²)	Damage threshold (MW/cm ²)
Ba ₆ Zn ₇ Ga ₂ S ₁₆	28.61	0.0707	40.47
AgGaS ₂	4.21	0.292	1.44

Table S8. The calculated total energies of model-0, model-1 and model-2 of Ba₆Zn₇Ga₂S₁₆, in which Zn(3) atom (Zn(1) and Zn(2): Wyckoff site 9b) taking any one of all three 3a Wyckoff sites (Zn(3), Ga(1) and Ga(2): Wyckoff site 3a) in the tetrahedral centre.

Comp.	model	Total energy (eV)
Ba ₆ Zn ₇ Ga ₂ S ₁₆	0	0
	1	0.67
	2	1.17